

Chao Zhang

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

597 papers	5,211 citations	37 h-index	50 g-index
769 ext. papers	6,704 ext. citations	2.6 avg, IF	5.97 L-index

#	Paper	IF	Citations
597	A Novel 700-V SOI LDMOS With Double-Sided Trench. <i>IEEE Electron Device Letters</i> , 2007 , 28, 422-424	4.4	82
596	New thin-film power MOSFETs with a buried oxide double step structure. <i>IEEE Electron Device Letters</i> , 2006 , 27, 377-379	4.4	80
595	High Reverse Blocking and Low Onset Voltage AlGaIn/GaN-on-Si Lateral Power Diode With MIS-Gated Hybrid Anode. <i>IEEE Electron Device Letters</i> , 2015 , 36, 660-662	4.4	76
594	High-Voltage LDMOS With Charge-Balanced Surface Low On-Resistance Path Layer. <i>IEEE Electron Device Letters</i> , 2009 , 30, 849-851	4.4	72
593	7.6 V Threshold Voltage High-Performance Normally-Off Al ₂ O ₃ /GaN MOSFET Achieved by Interface Charge Engineering. <i>IEEE Electron Device Letters</i> , 2016 , 37, 165-168	4.4	68
592	A Novel 220-GHz GaN Diode On-Chip Tripler With High Driven Power. <i>IEEE Electron Device Letters</i> , 2019 , 40, 780-783	4.4	67
591	Ultralow ON-Resistance High-Voltage p-Channel LDMOS With an Accumulation-Effect Extended Gate. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2614-2619	2.9	67
590	The research on 220GHz multicarrier high-speed communication system. <i>China Communications</i> , 2020 , 17, 131-139	3	66
589	. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2327-2334	2.9	63
588	A SiC Power MOSFET Loss Model Suitable for High-Frequency Applications. <i>IEEE Transactions on Industrial Electronics</i> , 2017 , 64, 8268-8276	8.9	61
587	Ultralow Specific On-Resistance High-Voltage SOI Lateral MOSFET. <i>IEEE Electron Device Letters</i> , 2011 , 32, 185-187	4.4	61
586	Normally OFF GaN-on-Si MIS-HEMTs Fabricated With LPCVD-SiNx Passivation and High-Temperature Gate Recess. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 614-619	2.9	60
585	A 1.6-V 25- μ S A 5-ppm/ μ S C Curvature-Compensated Bandgap Reference. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2012 , 59, 677-684	3.9	59
584	A new structure and its analytical model for the electric field and breakdown voltage of SOI high voltage device with variable-k dielectric buried layer. <i>Solid-State Electronics</i> , 2007 , 51, 493-499	1.7	59
583	. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1756-1761	2.9	57
582	New Superjunction LDMOS With N^+ -Type Charges Compensation Layer. <i>IEEE Electron Device Letters</i> , 2009 , 30, 305-307	4.4	56
581	Development of 340-GHz Transceiver Front End Based on GaAs Monolithic Integration Technology for THz Active Imaging Array. <i>Applied Sciences (Switzerland)</i> , 2020 , 10, 7924	2.6	55

580	High-Performance Enhancement-Mode Al ₂ O ₃ /AlGaIn/GaN-on-Si MISFETs With 626 MW/ cm^2 Figure of Merit. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 776-781	2.9	54
579	High-Voltage Thin-SOI LDMOS With Ultralow ON-Resistance and Even Temperature Characteristic. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1637-1643	2.9	53
578	Variation of Lateral Width Technique in Sol High-Voltage Lateral Double-Diffused MetalOxideSemiconductor Transistors Using High-k Dielectric. <i>IEEE Electron Device Letters</i> , 2015 , 36, 262-264	4.4	52
577	. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 4304-4308	2.9	51
576	An Ultrafast Adaptively Biased Capacitorless LDO With Dynamic Charging Control. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2012 , 59, 40-44	3.5	50
575	Breakdown-Voltage-Enhancement Technique for RF-Based AlGaIn/GaN HEMTs With a Source-Connected Air-Bridge Field Plate. <i>IEEE Electron Device Letters</i> , 2012 , 33, 670-672	4.4	49
574	An Ultralow-Power Fast-Transient Capacitor-Free Low-Dropout Regulator With Assistant PushPull Output Stage. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2013 , 60, 96-100	3.5	48
573	A Snapback Suppressed Reverse-Conducting IGBT With a Floating p-Region in Trench Collector. <i>IEEE Electron Device Letters</i> , 2012 , 33, 417-419	4.4	47
572	A 700- V Junction-Isolated Triple RESURF LDMOS With N-Type Top Layer. <i>IEEE Electron Device Letters</i> , 2014 , 35, 774-776	4.4	45
571	Equivalent Substrate Model for Lateral Super Junction Device. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 525-532	2.9	45
570	A new partial SOI power device structure with P-type buried layer. <i>Solid-State Electronics</i> , 2005 , 49, 1965-1968	1.7	45
569	Four-hundred gigahertz broadband multi-branch waveguide coupler. <i>IET Microwaves, Antennas and Propagation</i> , 2020 , 14, 1175-1179	1.6	44
568	An Advanced Spread Spectrum Architecture Using Pseudorandom Modulation to Improve EMI in Class D Amplifier. <i>IEEE Transactions on Power Electronics</i> , 2011 , 26, 638-646	7.2	43
567	. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 504-509	2.9	42
566	. <i>IEEE Electron Device Letters</i> , 2008 , 29, 1395-1397	4.4	40
565	Electric Field Distribution Around Drain-Side Gate Edge in AlGaIn/GaN HEMTs: Analytical Approach. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 3223-3229	2.9	39
564	Understanding switching losses in SiC MOSFET: Toward lossless switching 2015 ,		39
563	Folded-Accumulation LDMOST: New Power MOS Transistor With Very Low Specific On-Resistance. <i>IEEE Electron Device Letters</i> , 2009 , 30, 1329-1331	4.4	39

562	Comparing SiC switching power devices: MOSFET, NPN transistor and GTO thyristor. <i>Solid-State Electronics</i> , 2000 , 44, 325-340	1.7	39
561	GaN Power Integration for High Frequency and High Efficiency Power Applications: A Review. <i>IEEE Access</i> , 2020 , 8, 15529-15542	3.5	37
560	Improved double-recessed 4H-SiC MESFETs structure with recessed source/drain drift region. <i>Microelectronic Engineering</i> , 2007 , 84, 2888-2891	2.5	37
559	Mechanism of Ti/Al/Ti/W Au-free ohmic contacts to AlGaIn/GaN heterostructures via pre-ohmic recess etching and low temperature annealing. <i>Applied Physics Letters</i> , 2015 , 107, 262109	3.4	35
558	Schottky-Contact Technology in InAlN/GaN HEMTs for Breakdown Voltage Improvement. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1075-1081	2.9	35
557	A CMOS Voltage Reference Based on Mutual Compensation of V_{tn} and V_{tp} . <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2012 , 59, 341-345	3.5	34
556	. <i>IEEE Electron Device Letters</i> , 2012 , 33, 703-705	4.4	33
555	Area-Efficient Fast-Speed Lateral IGBT With a 3-D n-Region-Controlled Anode. <i>IEEE Electron Device Letters</i> , 2010 , 31, 467-469	4.4	33
554	Ultralow ON-Resistance SOI LDMOS With Three Separated Gates and High- ϵ_k Dielectric. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 3804-3807	2.9	33
553	Analytical Model and New Structure of the Variable- ϵ_k Dielectric Trench LDMOS With Improved Breakdown Voltage and Specific ON-Resistance. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 3334-3340	2.9	32
552	. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1438-1440	4.4	32
551	A High-Precision Compensated CMOS Bandgap Voltage Reference Without Resistors. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2010 , 57, 767-771	3.5	32
550	A new analytical model for optimizing SOI LDMOS with step doped drift region. <i>Microelectronics Journal</i> , 2006 , 37, 861-866	1.8	32
549	Large phase modulation of THz wave via an enhanced resonant active HEMT metasurface. <i>Nanophotonics</i> , 2018 , 8, 153-170	6.3	30
548	Challenges of future high power wireless power transfer for light-duty electric vehicles----technology and risk management. <i>ETransportation</i> , 2019 , 2, 100012	12.7	29
547	Novel Superjunction LDMOS (>950 V) With a Thin Layer SOI. <i>IEEE Electron Device Letters</i> , 2017 , 38, 1555-1558	4.5	29
546	High voltage REBULF LDMOS with N+ buried layer. <i>Solid-State Electronics</i> , 2010 , 54, 685-688	1.7	29
545	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 876-882	2.9	29

544	A Half-Select Disturb-Free 1T1R SRAM Cell With Built-In Write/Read-Assist Scheme for Ultralow-Voltage Operations. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2019 , 27, 2344-2353	2.6	27
543	High breakdown voltage 4H-SiC MESFETs with floating metal strips. <i>Microelectronic Engineering</i> , 2008 , 85, 89-92	2.5	27
542	Optimization of super-junction SOI-LDMOS with a step doping surface-implanted layer. <i>Semiconductor Science and Technology</i> , 2007 , 22, 464-470	1.8	27
541	SiC Trench MOSFET With Integrated Self-Assembled Three-Level Protection Schottky Barrier Diode. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 347-351	2.9	26
540	Analytical Modeling for a Novel Triple RESURF LDMOS With N-Top Layer. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2933-2939	2.9	26
539	A Closed-Form Charge Control Model for the Threshold Voltage of Depletion- and Enhancement-Mode AlGaIn/GaN Devices. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1607-1612	2.9	26
538	. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 2466-2472	2.9	25
537	Analytical models for the electric field distributions and breakdown voltage of Triple RESURF SOI LDMOS. <i>Solid-State Electronics</i> , 2012 , 69, 89-93	1.7	24
536	A mechanical reliability study of 3-dB waveguide hybrid couplers in submillimeter and terahertz bands. <i>Frontiers of Information Technology and Electronic Engineering</i> , 2021 , 22, 1104-1113	2.2	24
535	Device Technologies of GaN-on-Si for Power Electronics: Enhancement-Mode Hybrid MOS-HFET and Lateral Diode. <i>IEEE Transactions on Industrial Electronics</i> , 2017 , 64, 8971-8979	8.9	23
534	Theory of Superjunction With NFD and FD Modes Based on Normalized Breakdown Voltage. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 4114-4120	2.9	23
533	Band-to-Band Tunneling Injection Insulated-Gate Bipolar Transistor with a Soft Reverse-Recovery Built-In Diode. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1684-1686	4.4	23
532	A Novel 1200-V LDMOSFET With Floating Buried Layer in Substrate. <i>IEEE Electron Device Letters</i> , 2008 , 29, 645-647	4.4	23
531	Achieving Zero Switching Loss in Silicon Carbide MOSFET. <i>IEEE Transactions on Power Electronics</i> , 2019 , 34, 12193-12199	7.2	22
530	Characterization and Performance Evaluation of the Superjunction RB-IGBT in Matrix Converter. <i>IEEE Transactions on Power Electronics</i> , 2018 , 33, 3289-3301	7.2	22
529	A Novel Vertical Field Plate Lateral Device With Ultralow Specific On-Resistance. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 518-524	2.9	22
528	A 200-25-GHz Manifold-Coupled Multiplexer Utilizing Metal Waveguides. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2021 , 1-1	4.1	22
527	A novel double RESURF LDMOS and a versatile JFET device used as internal power supply and current detector for SPIC. <i>Microelectronics Journal</i> , 2006 , 37, 574-578	1.8	21

526	A Novel Virtual Sensing With Artificial Neural Network and K-Means Clustering for IGBT Current Measuring. <i>IEEE Transactions on Industrial Electronics</i> , 2018 , 65, 7343-7352	8.9	20
525	Optimization of Lateral Superjunction Based on the Minimum Specific ON-Resistance. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1984-1990	2.9	20
524	2018 ,		20
523	A Multiple-Ring-Modulated JTE Technique for 4H-SiC Power Device With Improved JTE-Dose Window. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 5042-5047	2.9	20
522	Numerical analysis on the 4H-SiC MESFETs with a source field plate. <i>Semiconductor Science and Technology</i> , 2007 , 22, 701-704	1.8	20
521	Ultralow-Contact-Resistance Au-Free Ohmic Contacts With Low Annealing Temperature on AlGaIn/GaN Heterostructures. <i>IEEE Electron Device Letters</i> , 2018 , 39, 847-850	4.4	19
520	A Resistorless High-Precision Compensated CMOS Bandgap Voltage Reference. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2019 , 66, 428-437	3.9	19
519	High-Resolution Wideband Phase Shifter With Current Limited Vector-Sum. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2019 , 66, 820-833	3.9	19
518	A Novel High Voltage Ultra-Thin SOI-LDMOS With Sectional Linearly Doped Drift Region. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1151-1154	4.4	19
517	An AlGaIn/GaN HEMT with a reduced surface electric field and an improved breakdown voltage. <i>Chinese Physics B</i> , 2012 , 21, 086105	1.2	19
516	The future of bipolar power transistors. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 2535-2543	2.9	19
515	Design and Experimental Verification of an Efficient SSCB Based on CS-MCT. <i>IEEE Transactions on Power Electronics</i> , 2020 , 35, 11682-11693	7.2	19
514	Investigation of the interface between LPCVD-SiNx gate dielectric and III-nitride for AlGaIn/GaN MIS-HEMTs. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 041202	1.3	19
513	. <i>IEEE Electron Device Letters</i> , 2018 , 39, 252-255	4.4	18
512	A High-Voltage LDMOS Compatible With High-Voltage Integrated Circuits on p-Type SOI Layer. <i>IEEE Electron Device Letters</i> , 2009 , 30, 1093-1095	4.4	18
511	A behavioral model for MCT surge current analysis in pulse discharge. <i>Solid-State Electronics</i> , 2014 , 99, 31-37	1.7	17
510	2008 ,		17
509	Back-Gate Effect on $R_{\text{ON,sp}}$ and BV for Thin Layer SOI Field p-Channel LDMOS. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 1098-1104	2.9	16

508	Analytical Switching Loss Model for GaN-Based Control Switch and Synchronous Rectifier in Low-Voltage Buck Converters. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2019 , 7, 1485-1495	5.6	16
507	High-Voltage SOI SJ-LDMOS With a Nondepletion Compensation Layer. <i>IEEE Electron Device Letters</i> , 2009 , 30, 68-71	4.4	16
506	An Ultralow Loss Superjunction Reverse Blocking Insulated-Gate Bipolar Transistor With Shorted-Collector Trench. <i>IEEE Electron Device Letters</i> , 2016 , 37, 1462-1465	4.4	16
505	Simulation study on AlGaIn/GaN diode with E-shaped anode for ultra-low turn-on voltage. <i>Superlattices and Microstructures</i> , 2018 , 117, 330-335	2.8	15
504	220 GHz outdoor wireless communication system based on a Schottky-diode transceiver. <i>IEICE Electronics Express</i> , 2016 , 13, 20160282-20160282	0.5	15
503	High Peak Current MOS Gate-Triggered Thyristor With Fast Turn-On Characteristics for Solid-State Closing Switch Applications. <i>IEEE Electron Device Letters</i> , 2016 , 37, 205-208	4.4	15
502	A Resistorless Low-Power Voltage Reference. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2016 , 63, 613-617	3.5	15
501	A Resistorless CMOS Voltage Reference Based on Mutual Compensation of V_{T} and V_{TH} . <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2013 , 60, 582-586	3.5	15
500	Design and Characterization of High di/dt CS-MCT for Pulse Power Applications. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 4206-4212	2.9	15
499	A novel substrate-assisted RESURF technology for small curvature radius junction 2011 ,		15
498	Two-dimensional analysis of the surface state effects in 4H-SiC MESFETs. <i>Microelectronic Engineering</i> , 2008 , 85, 295-299	2.5	15
497	A High-Precision Resistor-Less CMOS Compensated Bandgap Reference Based on Successive Voltage-Step Compensation. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2018 , 65, 4086-4096	3.9	15
496	Investigation of Bulk Traps by Conductance Method in the Deep Depletion Region of the AlO/GaN MOS Device. <i>Nanoscale Research Letters</i> , 2017 , 12, 342	5	14
495	Ultralow-power fast-transient output-capacitor-less low-dropout regulator with advanced adaptive biasing circuit. <i>IET Circuits, Devices and Systems</i> , 2015 , 9, 172-180	1.1	14
494	Investigation and Failure Mode of Asymmetric and Double Trench SiC mosfets Under Avalanche Conditions. <i>IEEE Transactions on Power Electronics</i> , 2020 , 35, 8524-8531	7.2	14
493	The $R_{ON,min}$ of Balanced Symmetric Vertical Super Junction Based on R-Well Model. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 224-230	2.9	14
492	A novel substrate termination technology for lateral double-diffused MOSFET based on curved junction extension. <i>Semiconductor Science and Technology</i> , 2014 , 29, 045002	1.8	14
491	SLOP-LDMOS - a novel super-junction concept LDMOS and its experimental demonstration		14

490	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1390-1395	2.9	14
489	Non-full depletion mode and its experimental realization of the lateral superjunction 2018 ,		13
488	Novel Low-Resistance Current Path UMOS With High-K Dielectric Pillars. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 2840-2846	2.9	13
487	High-voltage thick layer SOI technology for PDP scan driver IC 2011 ,		13
486	All-GaN Power Integration: Devices to Functional Subcircuits and Converter ICs. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2020 , 8, 31-41	5.6	13
485	AlGaIn/GaN MIS-HEMT With AlN Interface Protection Layer and Trench Termination Structure. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 5203-5207	2.9	13
484	. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 217-223	2.9	12
483	Total-Ionizing-Dose Irradiation-Induced Dielectric Field Enhancement for High-Voltage SOI LDMOS. <i>IEEE Electron Device Letters</i> , 2019 , 40, 593-596	4.4	12
482	250 V Thin-Layer SOI Technology With Field pLDMOS for High-Voltage Switching IC. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 1970-1976	2.9	12
481	A Carrier Stored SOI LIGBT With Ultralow ON-State Voltage and High Current Capability. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 3365-3370	2.9	12
480	High Breakdown Voltage and Low Dynamic ON-Resistance AlGaIn/GaN HEMT with Fluorine Ion Implantation in SiN Passivation Layer. <i>Nanoscale Research Letters</i> , 2019 , 14, 191	5	12
479	A Snapback-Free Fast-Switching SOI LIGBT With Polysilicon Regulative Resistance and Trench Cathode. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3961-3966	2.9	12
478	Ultralow Turn-OFF Loss SOI LIGBT With p-Buried Layer During Inductive Load Switching. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 3774-3780	2.9	12
477	Electro-thermal analytical model and simulation of the self-heating effects in multi-finger 4H-SiC power MESFETs. <i>Semiconductor Science and Technology</i> , 2007 , 22, 1339-1343	1.8	12
476	An analysis and experimental approach to MOS controlled diodes behavior. <i>IEEE Transactions on Power Electronics</i> , 2000 , 15, 916-922	7.2	12
475	Accumulation mode triple gate SOI LDMOS with ultralow on-resistance and enhanced transconductance 2016 ,		12
474	Embedded Hardware Artificial Neural Network Control for Global and Real-Time Imbalance Current Suppression of Parallel Connected IGBTs. <i>IEEE Transactions on Industrial Electronics</i> , 2020 , 67, 2186-2196 ^{8.9}		12
473	Investigation on the Long-Term Reliability of High-Voltage p-GaN HEMT by Repetitively Transient Overcurrent. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 5322-5328	2.9	12

472	Evaluation of CS-MCT in DC Solid-State Circuit Breaker Applications. <i>IEEE Transactions on Industry Applications</i> , 2018 , 54, 5465-5473	4.3	12
471	Asymmetric 3D tri-gate 4H-SiC MESFETs with a recessed drain drift region. <i>Semiconductor Science and Technology</i> , 2009 , 24, 045001	1.8	11
470	. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 3033-3043	2.9	11
469	Design of a low noise 190-40 GHz subharmonic mixer based on 3D geometric modeling of Schottky diodes and CAD load-pull techniques. <i>IEICE Electronics Express</i> , 2016 , 13, 20160604-20160604	0.5	10
468	Analytical model and new structure of the enhancement-mode polarization-junction HEMT with vertical conduction channel. <i>Superlattices and Microstructures</i> , 2016 , 92, 92-99	2.8	10
467	A Snapback-Free Fast-Switching SOI LIGBT With an Embedded Self-Biased n-MOS. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 3572-3576	2.9	10
466	Investigation on total-ionizing-dose radiation response for high voltage ultra-thin layer SOI LDMOS 2018 ,		10
465	A snapback suppressed reverse-conducting IGBT with soft reverse recovery characteristic. <i>Superlattices and Microstructures</i> , 2013 , 61, 59-68	2.8	10
464	A Method to Prevent Strong Snapback in LDNMOS for ESD Protection. <i>IEEE Transactions on Device and Materials Reliability</i> , 2013 , 13, 50-53	1.6	10
463	3-D Edge Termination Design and R_{ON} -BV Model of A 700-V Triple RESURF LDMOS With N-Type Top Layer. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2579-2586	2.9	9
462	Proposal of a novel enhancement type AlGaIn/GaN HEMT using recess-free field coupled gate. <i>Superlattices and Microstructures</i> , 2018 , 122, 343-348	2.8	9
461	Design of a 1200-V ultra-thin partial SOI LDMOS with n-type buried layer. <i>Superlattices and Microstructures</i> , 2014 , 75, 796-805	2.8	9
460	A review of HVI technology. <i>Microelectronics Reliability</i> , 2014 , 54, 2704-2716	1.2	9
459	Realizing high breakdown voltage for a novel interface charges islands structure based on partial-SOI substrate. <i>Microelectronics Reliability</i> , 2012 , 52, 692-697	1.2	9
458	Study of the breakdown failure mechanisms for power AlGaIn/GaN HEMTs implemented using a RF compatible process. <i>Microelectronics Reliability</i> , 2012 , 52, 964-968	1.2	9
457	High dV/dt immunity MOS controlled thyristor using a double variable lateral doping technique for capacitor discharge applications. <i>Chinese Physics B</i> , 2014 , 23, 077307	1.2	9
456	Partial SOI power LDMOS with a variable low-k dielectric buried layer and a buried p-layer 2010 ,		9
455	Improved performance of 4H-SiC metal-semiconductor field-effect transistors with step p-buffer layer. <i>Chinese Physics B</i> , 2011 , 20, 017304	1.2	9

454	A new SOI high-voltage device with a step-thickness drift region and its analytical model for the electric field and breakdown voltage. <i>Semiconductor Science and Technology</i> , 2008 , 23, 035028	1.8	9
453	190 GHz high power input frequency doubler based on Schottky diodes and AlN substrate. <i>IEICE Electronics Express</i> , 2016 , 13, 20160981-20160981	0.5	9
452	Experimentally demonstrate a cathode short MOS-controlled thyristor (CS-MCT) for single or repetitive pulse applications 2016 ,		9
451	An Efficient and Reliable Solid-State Circuit Breaker Based on Mixture Device. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 9767-9771	7.2	9
450	Simulation design of uniform low turn-on voltage and high reverse blocking AlGaIn/GaN power field effect rectifier with trench heterojunction anode. <i>Superlattices and Microstructures</i> , 2017 , 105, 132-138	2.8	8
449	A Novel Insulated Gate Triggered Thyristor With Schottky Barrier for Improved Repetitive Pulse Life and High-di/dt Characteristics. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1018-1025	2.9	8
448	Novel Silicon-Controlled Rectifier With Snapback-Free Performance for High-Voltage and Robust ESD Protection. <i>IEEE Electron Device Letters</i> , 2019 , 40, 435-438	4.4	8
447	A novel 4H-SiC trench MOSFET with double shielding structures and ultralow gate-drain charge. <i>Journal of Semiconductors</i> , 2019 , 40, 052803	2.3	8
446	Charge storage impact on input capacitance in p-GaN gate AlGaIn/GaN power high-electron-mobility transistors. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 305106	3	8
445	Experimental Study of 600 V Accumulation-Type Lateral Double-Diffused MOSFET With Ultra-Low On-Resistance. <i>IEEE Electron Device Letters</i> , 2020 , 41, 465-468	4.4	8
444	. <i>IEEE Electron Device Letters</i> , 2016 , 37, 1185-1188	4.4	8
443	Edge termination design of a 700-V triple RESURF LDMOS with n-type top layer 2017 ,		8
442	A Controllable High-Voltage C-SenseFET by Inserting the Second Gate. <i>IEEE Transactions on Power Electronics</i> , 2011 , 26, 1329-1332	7.2	8
441	A novel high-voltage light punch-through carrier stored trench bipolar transistor with buried p-layer. <i>Chinese Physics B</i> , 2012 , 21, 068504	1.2	8
440	Optimization and Experiments of Lateral Semi-Superjunction Device Based on Normalized Current-Carrying Capability. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1969-1972	4.4	8
439	Rejection of Spoof SPPs Using the Second Resonant Mode of Vertical Split-Ring Resonator. <i>IEEE Microwave and Wireless Components Letters</i> , 2019 , 29, 23-25	2.6	8
438	Failure Mechanism of Avalanche Condition for 1200-V Double Trench SiC MOSFET. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2021 , 9, 2147-2154	5.6	8
437	Optimal Slope Ranking: An Approximate Computing Approach for Circuit Pruning 2018 ,		8

436	Simulation Study of an Ultralow Switching Loss p-GaN Gate HEMT With Dynamic Charge Storage Mechanism. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 175-183	2.9	8
435	A Novel Low VF Super Barrier Rectifier (SBR) With an N-Enhancement Layer. <i>IEEE Electron Device Letters</i> , 2017 , 38, 244-247	4.4	7
434	An Extraction Method for the Interface Acceptor Distribution of GaN MOS-HEMT. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4164-4169	2.9	7
433	A Novel 3-dB Waveguide Hybrid Coupler for Terahertz Operation. <i>IEEE Microwave and Wireless Components Letters</i> , 2019 , 29, 273-275	2.6	7
432	Over 1.1 kV breakdown low turn-on voltage GaN-on-Si power diode with MIS-Gated hybrid anode 2015 ,		7
431	Improved Model for Ionization-Induced Surface Recombination Current in p-n-p BJTs. <i>IEEE Transactions on Nuclear Science</i> , 2020 , 67, 1826-1834	1.7	7
430	Ultrathin-Barrier AlGaIn/GaN Hybrid-Anode-Diode With Optimized Barrier Thickness for Zero-Bias Microwave Mixer. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 828-833	2.9	7
429	A split gate vertical GaN power transistor with intrinsic reverse conduction capability and low gate charge 2018 ,		7
428	Impact of Termination Region on Switching Loss for SiC MOSFET. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1026-1031	2.9	7
427	High voltage InAlN/GaN HEMTs with nonalloyed Source/Drain for RF power applications. <i>Solid-State Electronics</i> , 2014 , 91, 19-23	1.7	7
426	2014 ,		7
425	A snapback suppressed reverse-conducting IGBT with built-in diode by utilizing edge termination. <i>Superlattices and Microstructures</i> , 2014 , 70, 109-116	2.8	7
424	A novel 700V deep trench isolated double RESURF LDMOS with P-sink layer 2017 ,		7
423	A snapback-free RC-IGBT with Alternating N/P buffers 2017 ,		7
422	. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1174-1176	4.4	7
421	A 1.6-V 17- μ A 5.2-ppm/ $^{\circ}$ C bandgap reference with mutative curvature-compensation. <i>International Journal of Electronics</i> , 2012 , 99, 519-530	1.2	7
420	Single capacitor with current amplifier compensation for ultra-large capacitive load three-stage amplifier. <i>Microelectronics Journal</i> , 2013 , 44, 712-717	1.8	7
419	An AlGaIn/GaN HEMT with enhanced breakdown and a near-zero breakdown voltage temperature coefficient. <i>Chinese Physics B</i> , 2013 , 22, 026103	1.2	7

418	Uniform and linear variable doping ultra-thin PSOI LDMOS with n-type buried layer. <i>Electronics Letters</i> , 2013 , 49, 1407-1409	1.1	7
417	A novel analytical model of the vertical breakdown voltage on impurity concentration in top silicon layer for SOI high voltage devices. <i>International Journal of Electronics</i> , 2011 , 98, 973-980	1.2	7
416	Breakdown voltage model and structure realization of a thin silicon layer with linear variable doping on a silicon on insulator high voltage device with multiple step field plates. <i>Chinese Physics B</i> , 2012 , 21, 108502	1.2	7
415	Two-dimensional analysis of the gate-source distance scaling effects in 4H-SiC MESFETs. <i>Semiconductor Science and Technology</i> , 2009 , 24, 015011	1.8	7
414	Improved Characteristics of 4H-SiC MESFET with Multi-recessed Drift Region 2007 ,		7
413	Development of High Power 220 GHz Frequency Triplers Based on Schottky Diodes. <i>IEEE Access</i> , 2020 , 8, 74401-74412	3.5	7
412	A Constant On-Time Control With Internal Active Ripple Compensation Strategy for Buck Converter With Ceramic Capacitors. <i>IEEE Transactions on Power Electronics</i> , 2019 , 34, 9263-9278	7.2	7
411	Analyses and Experiments of the Schottky Contact Super Barrier Rectifier (SSBR). <i>IEEE Electron Device Letters</i> , 2017 , 38, 902-905	4.4	6
410	Experiments of a Novel low on-resistance LDMOS with 3-D Floating Vertical Field Plate 2019 ,		6
409	A Novel CSTBT with Hole Barrier for High dV/dt Controllability and Low EMI Noise 2019 ,		6
408	A Nanoscale Low-Power Resistorless Voltage Reference with High PSRR. <i>Nanoscale Research Letters</i> , 2019 , 14, 33	5	6
407	Shield Gate Trench MOSFET With Narrow Gate Architecture and Low-k Dielectric Layer. <i>IEEE Electron Device Letters</i> , 2020 , 41, 749-752	4.4	6
406	. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 1856-1861	2.9	6
405	An Accumulation Mode RF Laterally Double Diffused MOSFET With Improved Performance. <i>IEEE Electron Device Letters</i> , 2016 , 37, 1321-1323	4.4	6
404	Ultralow specific on-resistance high voltage LDMOS with a variable-K dielectric trench 2014 ,		6
403	A Bi-directional Electric Field Enhanced Field Stop Reverse Blocking IGBT 2014 ,		6
402	The Investigation of a New NO ₂ OTFT Sensor Based on Heterojunction F16CuPc/CuPc Thin Films. <i>Advanced Materials Research</i> , 2013 , 721, 159-163	0.5	6
401	2017 ,		6

400	A high-performance GaN E-mode reverse blocking MISHEMT with MIS field effect drain for bidirectional switch 2017 ,		6
399	Hot-carrier-induced linear drain current and threshold voltage degradation for thin layer silicon-on-insulator field P-channel lateral double-diffused metal-oxide-semiconductor. <i>Applied Physics Letters</i> , 2015 , 107, 203507	3.4	6
398	Design of a 700 V DB-nLDMOS Based on Substrate Termination Technology. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 4121-4127	2.9	6
397	700 V ultra-low on-resistance DB-nLDMOS with optimised thermal budget and neck region. <i>Electronics Letters</i> , 2014 , 50, 209-211	1.1	6
396	Dual-gate lateral double-diffused metaloxide semiconductor with ultra-low specific on-resistance. <i>Chinese Physics B</i> , 2013 , 22, 048501	1.2	6
395	Novel high-voltage power device based on self-adaptive interface charge. <i>Chinese Physics B</i> , 2011 , 20, 027101	1.2	6
394	The SuperJunction MOS-controlled thyristor (SJ-MCT) with low power loss for high-power switching applications 2012 ,		6
393	A New Reduced Bulk Field (REBULF) High-Voltage LDMOS with N+-Floating Layer 2006 ,		6
392	Novel Homogenization Field Technology in Lateral Power Devices. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1677-1680	4.4	6
391	A Novel Ultralow RON,sp Triple RESURF LDMOS With Sandwich n-p-n Layer. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 5605-5612	2.9	6
390	Threshold voltage modulation by interface charge engineering for high performance normally-off GaN MOSFETs with high faulty turn-on immunity 2016 ,		6
389	Gate sensed method of load current imbalance measuring for paralleling IGBT devices 2016 ,		6
388	Mode Analyzing Method for Fast Design of Branch Waveguide Coupler. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2019 , 67, 4733-4740	4.1	6
387	Physics-Based 2-D Analytical Model for Field-Plate Engineering of AlGaIn/GaN Power HFET. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 116-125	2.9	6
386	Ultrafast and Low-Turn-OFF Loss Lateral IEGT With a MOS-Controlled Shorted Anode. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 533-538	2.9	6
385	A Novel IGBT with Self-Regulated Potential for Extreme Low EMI Noise. <i>IEEE Electron Device Letters</i> , 2018 , 1-1	4.4	6
384	WR-2.8 Band Pseudoelliptic Waveguide Filter Based on Singlet and Extracted Pole Resonator. <i>IEEE Access</i> , 2019 , 7, 54705-54711	3.5	5
383	Vertical GaN Power Transistor With Intrinsic Reverse Conduction and Low Gate Charge for High-Performance Power Conversion. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2019 , 7, 1449-1455	5.6	5

- 382 An Advanced Bootstrap Circuit for High Frequency, High Area-Efficiency and Low EMI Buck Converter. *IEEE Transactions on Circuits and Systems II: Express Briefs*, **2019**, 66, 858-862 3.5 5
- 381 A Neural Network Assistance AMPPT Solar Energy Harvesting System With 89.39% Efficiency and 0.010.5% Tracking Errors. *IEEE Transactions on Circuits and Systems I: Regular Papers*, **2020**, 67, 2960-2974 3.9 5
- 380 Tri-Gated Hybrid Anode AlGaIn/GaN Power Diode With Intrinsic Low Turn-on Voltage and Ultralow Reverse Leakage Current. *IEEE Transactions on Electron Devices*, **2020**, 67, 1712-1717 2.9 5
- 379 Total Ionizing Dose Effects in 30-V Split-Gate Trench VDMOS. *IEEE Transactions on Nuclear Science*, **2020**, 67, 2009-2014 1.7 5
- 378 Concept and design of super junction devices. *Journal of Semiconductors*, **2018**, 39, 021001 2.3 5
- 377 Development of GaN Power IC Platform and All GaN DC-DC Buck Converter IC **2019**, 5
- 376 Ultra-Low Specific On-resistance Lateral Double-Diffused Metal-Oxide-Semiconductor Transistor with Enhanced Dual-Gate and Partial P-buried Layer. *Nanoscale Research Letters*, **2019**, 14, 38 5 5
- 375 Low specific on-resistance power MOSFET with a surface improved super-junction layer. *Superlattices and Microstructures*, **2014**, 72, 1-10 2.8 5
- 374 A new analytical model for the surface electric field distribution and breakdown voltage of the SOI trench LDMOS. *Chinese Physics B*, **2012**, 21, 078502 1.2 5
- 373 High-voltage super-junction lateral double-diffused metal-oxide semiconductor with a partial lightly doped pillar. *Chinese Physics B*, **2013**, 22, 068501 1.2 5
- 372 New Lateral IGBT with Controlled Anode on SOI substrate for PDP scan driver IC **2009**, 5
- 371 Eliminating Back-Gate Bias Effects in a Novel SOI High-Voltage Device Structure. *IEEE Transactions on Electron Devices*, **2009**, 56, 1659-1666 2.9 5
- 370 A 188 V 7.2 mm², P-channel high voltage device formed on an epitaxy-SIMOX substrate. *Chinese Physics B*, **2011**, 20, 087101 1.2 5
- 369 A 700 V BCD technology platform for high voltage applications. *Journal of Semiconductors*, **2012**, 33, 044004 2.3 5
- 368 A 1.8-V 0.7 ppm/°C high order temperature-compensated CMOS current reference. *Analog Integrated Circuits and Signal Processing*, **2007**, 51, 175-179 1.2 5
- 367 Realizing high voltage SJ-LDMOS with non-uniform N-buried layer. *Solid-State Electronics*, **2008**, 52, 675-678 5
- 366 Novel Self-Modulated Lateral Superjunction Device Suppressing the Inherent 3-D JFET Effect. *IEEE Electron Device Letters*, **2020**, 41, 1392-1395 4.4 5
- 365 A Study on Ionization Damage Effects of Anode-Short MOS-Controlled Thyristor. *IEEE Transactions on Nuclear Science*, **2020**, 67, 2062-2072 1.7 5

364	Suppression of Hot-Hole Injection in High-Voltage Triple RESURF LDMOS With Sandwich N-P-N Layer: Toward High-Performance and High-Reliability 2020 ,		5
363	High-Performance Ultrathin-Barrier AlGaIn/GaN Hybrid Anode Diode With Al _{0.2} In _{0.8} Gate Dielectric and In Situ SiN ₂ Cap Passivation. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 4136-4140	2.9	5
362	A Fast-Transient Low-Dropout Regulator With Current-Efficient Super Transconductance Cell and Dynamic Reference Control. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2021 , 68, 2354-2367	3.9	5
361	. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 8300-8307	7.2	5
360	Model and Experiments of Small-Size Vertical Devices With Field Plate. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1416-1421	2.9	5
359	High Voltage Insulated Gate Trigger Thyristor With High-Efficiency Injection for Fast Turn-on and High Current Pulse. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1965-1968	4.4	5
358	Direct extraction method of HEMT switch small-signal model with multiparasitic capacitive current path. <i>International Journal of RF and Microwave Computer-Aided Engineering</i> , 2019 , 29, e21690	1.5	5
357	Design of an Isolated Circuit Breaker With Robust Interruption Capability for DC Microgrid Protection. <i>IEEE Transactions on Industrial Electronics</i> , 2021 , 68, 12408-12417	8.9	5
356	A 220-GHz Third-Harmonic Mixer Based on Balanced Structure and Hybrid Transmission Line. <i>IEEE Access</i> , 2019 , 7, 50007-50011	3.5	4
355	High performance enhancement-mode HEMT with 3DEG to conduct current and 3DHG as back barrier. <i>Superlattices and Microstructures</i> , 2019 , 130, 437-445	2.8	4
354	Multizone Gradient-Modulated Guard Ring Technique for Ultrahigh Voltage 4H-SiC Devices With Increased Tolerances to Implantation Dose and Surface Charges. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2019 , 7, 1505-1512	5.6	4
353	Accumulation-mode high voltage SOI LDMOS with ultralow specific on-resistance 2015 ,		4
352	Design and Experimental Demonstration of Integrated Over-Current Protection Circuit for GaN DC/DC Converters. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2020 , 8, 4270-4278	5.6	4
351	A novel low turnoff loss carrier stored SOI LIGBT with trench gate barrier. <i>Superlattices and Microstructures</i> , 2016 , 89, 179-187	2.8	4
350	Observation of self-recoverable gate degradation in p-GaN AlGaIn/GaN HEMTs after long-term forward gate stress: The trapping & detrapping dynamics of hole/electron 2019 ,		4
349	Embedded capacitor multiplier gain boosting compensation for large-capacitive-load three-stage amplifier with slew rate enhancement. <i>Analog Integrated Circuits and Signal Processing</i> , 2014 , 79, 543-553	1.2	4
348	Design of highly integrated power management unit with dual DVS-enabled regulators. <i>Analog Integrated Circuits and Signal Processing</i> , 2014 , 80, 209-220	1.2	4
347	Digital Error Corrector for Phase Lead-Compensated Buck Converter in DVS Applications. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2013 , 21, 1747-1751	2.6	4

346	Ultra-low specific on-resistance SOI high voltage trench LDMOS with dielectric field enhancement based on ENBULF concept 2013 ,		4
345	High-power SiC MESFET using a dual p-buffer layer for an S-band power amplifier. <i>Chinese Physics B</i> , 2013 , 22, 017302	1.2	4
344	Transient overvoltage induced failure of MOS-controlled thyristor under ultra-high di/dt condition 2017 ,		4
343	A snapback suppressed reverse-conducting IGBT with uniform temperature distribution. <i>Chinese Physics B</i> , 2014 , 23, 018505	1.2	4
342	Dual-Miller Parallel Compensation for Low-Power Three-Stage Amplifier with a Wide Range of Capacitive Loads. <i>Circuits, Systems, and Signal Processing</i> , 2014 , 33, 287-297	2.2	4
341	A fully on-chip 1-W capacitor-free low-dropout regulator with adaptive output stage. <i>Analog Integrated Circuits and Signal Processing</i> , 2014 , 78, 353-360	1.2	4
340	A 3.2ppm/°C curvature-compensated bandgap reference with wide supply voltage range. <i>Microelectronics Journal</i> , 2012 , 43, 863-868	1.8	4
339	A high reliable reverse-conducting IGBT with a floating P-plug 2013 ,		4
338	Low-cost low-power HV startup circuit with 50 V pJFET and 700 V T-nJFET. <i>Electronics Letters</i> , 2013 , 49, 1318-1320	1.1	4
337	Small-sized silicon-on-insulator lateral insulated gate bipolar transistor for larger forward bias safe operating area and lower turnoff energy. <i>Micro and Nano Letters</i> , 2013 , 8, 386-389	0.9	4
336	High-voltage SOI lateral MOSFET with a dual vertical field plate. <i>Chinese Physics B</i> , 2013 , 22, 118502	1.2	4
335	Investigation of device geometry- and temperature-dependent characteristics of AlGaN/GaN lateral field-effect rectifier. <i>Semiconductor Science and Technology</i> , 2013 , 28, 015021	1.8	4
334	A low-power ultra-fast capacitor-less LDO with advanced dynamic push-pull techniques 2011 ,		4
333	Design and optimization of linearly graded-doping junction termination extension for 3.3-kV-class IGBTs. <i>Journal of Semiconductors</i> , 2011 , 32, 124004	2.3	4
332	A 300 V thin layer SOI nLDMOS based on RESURF and MFP 2012 ,		4
331	A low on-resistance SOI LDMOS using a trench gate and a recessed drain. <i>Journal of Semiconductors</i> , 2012 , 33, 074005	2.3	4
330	High voltage SOI SJ-LDMOS on composite substrate 2009 ,		4
329	A novel spread-spectrum clock generator for suppressing conducted EMI in switching power supply. <i>Microelectronics Journal</i> , 2010 , 41, 93-98	1.8	4

328	Realization of over 650V double RESURF LDMOS with HVI for high side gate drive IC 2006 ,		4
327	Total Dose Radiation Characteristics of High Voltage LDMOS on SIMOX Substrate 2007 ,		4
326	A Novel Thyristor-Based Bidirectional SSCB With Controllable Current Breaking Capability. <i>IEEE Transactions on Power Electronics</i> , 2022 , 37, 4526-4534	7.2	4
325	Electrostatic Discharge (ESD) Behavior of p-GaN HEMTs 2020 ,		4
324	Novel high voltage RESURF AlGaN/GaN HEMT with charged buffer layer. <i>Science China Information Sciences</i> , 2016 , 59, 1	3.4	4
323	Design of a novel triple reduced surface field LDMOS with partial linear variable doping n-type top layer. <i>Superlattices and Microstructures</i> , 2016 , 93, 242-247	2.8	4
322	A 1.8 V 0.918 ppm/°C CMOS bandgap voltage reference with curvature-compensated. <i>IEICE Electronics Express</i> , 2019 , 16, 20190616-20190616	0.5	4
321	Transient Response Improvement of DC-DC Converter by Current Mode Variable on Time Control 2018 ,		4
320	A High Bidirectional Blocking Capability Insulated-Gate Bipolar Transistor With Ultralow Loss. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4729-4733	2.9	4
319	Design Techniques of Sub-ns Level Shifters With Ultrahigh dV/dt Immunity for Various Wide-Bandgap Applications. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 10447-10460	7.2	4
318	Gate field plate IGBT with trench accumulation layer for extreme injection enhancement. <i>Superlattices and Microstructures</i> , 2017 , 104, 54-62	2.8	3
317	Over Kilovolt GaN Vertical Super-Junction Trench MOSFET: Approach for Device Design and Optimization 2019 ,		3
316	Low On-state Voltage and Latch-up Immunity Thin SOI LIGBT with Multi-Segmented Trench Gates 2019 ,		3
315	An Ultralow Loss Insulated Gate Bipolar Transistor With Emitter Dual Injection. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4314-4319	2.9	3
314	Novel High-Holding Voltage SCR with Embedded Carrier Recombination Structure for Latch-up Immune and Robust ESD Protection. <i>Nanoscale Research Letters</i> , 2019 , 14, 175	5	3
313	A Fully-Integrated Optoelectronic Detector With High Gain Bandwidth Product. <i>IEEE Access</i> , 2019 , 7, 53032-53039	3.5	3
312	A New Design Method for Solar Energy Harvesting System Based on Neural Network 2019 ,		3
311	Analysis of simulation approaches for the breakdown characteristics of SOI high-voltage PMOS in a fixed power supply. <i>Superlattices and Microstructures</i> , 2015 , 78, 50-60	2.8	3

310	2020,		3
309	High Performance of Trench Schottky Contact Super Barrier Rectifier With a p-Injector. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 215-222	2.9	3
308	A high-voltage half-bridge gate drive circuit for GaN devices with high-speed low-power and high-noise-immunity level shifter 2018 ,		3
307	AlGaIn/GaN Lateral CRDs With Hybrid Trench Cathodes. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2660-2665	2.9	3
306	An Injection Enhanced LIGBT on Thin SOI Layer Compatible With CMOS Process. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 2681-2685	2.9	3
305	A Snapback-Free Reverse-Conducting IGBT with Integrated Schottky Diode in the Collector 2019 ,		3
304	A novel SON LDMOS with Triple-RESURF technology. <i>Superlattices and Microstructures</i> , 2014 , 75, 151-158.	2.8	3
303	Design and optimization of linearly graded field limiting ring termination for high-voltage SiC diodes 2014 ,		3
302	A non-Ohmic normally-off GaN monolithic bidirectional switch with MIS field effect schottky tunnel junction. <i>Superlattices and Microstructures</i> , 2017 , 109, 414-422	2.8	3
301	2017,		3
300	High Performance Enhancement-Mode AlGaIn/GaN MIS-HEMT with Selective Fluorine Treatment. <i>Advances in Condensed Matter Physics</i> , 2015 , 2015, 1-7	1	3
299	Experimental and numerical analyses of high voltage 4H-SiC junction barrier Schottky rectifiers with linearly graded field limiting ring. <i>Chinese Physics B</i> , 2014 , 23, 057203	1.2	3
298	A new high-side and low-side LDMOST with a selective buried layer in the substrate. <i>Superlattices and Microstructures</i> , 2014 , 76, 288-296	2.8	3
297	An L-shaped low on-resistance current path SOI LDMOS with dielectric field enhancement. <i>Journal of Semiconductors</i> , 2014 , 35, 034011	2.3	3
296	Adaptive duty ratio modulation technique in switching DCDC converter operating in discontinuous conduction mode. <i>Analog Integrated Circuits and Signal Processing</i> , 2014 , 78, 361-371	1.2	3
295	A resistorless CMOS bandgap reference with low temperature coefficient and high PSRR. <i>International Journal of Electronics</i> , 2012 , 99, 1427-1438	1.2	3
294	A High Figure-of-Merit SOI MOSFET with a Double-Sided Charge Oxide-Trench. <i>Chinese Physics Letters</i> , 2013 , 30, 088503	1.8	3
293	An Inductive Kickback Absorption Scheme Without Power Zener and Large Capacitor. <i>IEEE Transactions on Industrial Electronics</i> , 2011 , 58, 709-716	8.9	3

292	A high efficiency synchronous buck converter with adaptive dead time control for dynamic voltage scaling applications 2011 ,		3
291	A 1.3 ppm/°C BiCMOS bandgap voltage reference using piecewise-exponential compensation technique. <i>Analog Integrated Circuits and Signal Processing</i> , 2011 , 66, 171-176	1.2	3
290	A novel complementary N+-charge island SOI high voltage device. <i>Journal of Semiconductors</i> , 2010 , 31, 114010	2.3	3
289	700 V segmented anode LIGBT with low on-resistance and onset Voltage 2010 ,		3
288	Application of field plate in SLOP-LDMOS 2010 ,		3
287	Application of spread spectrum for EMI reduction in class D amplifier 2010 ,		3
286	Research on periodic switching frequency modulation for conducted EMI suppressing in power converter. <i>Microelectronics Journal</i> , 2011 , 42, 415-421	1.8	3
285	Design of a 1200-V Thin-Silicon-Layer p-Channel SOI LDMOS Device. <i>Chinese Physics Letters</i> , 2011 , 28, 128503	1.8	3
284	Ultra-low specific on-resistance SOI double-gate trench-type MOSFET. <i>Journal of Semiconductors</i> , 2011 , 32, 104004	2.3	3
283	Design of 700 V triple RESURF nLDMOS with low on-resistance. <i>Journal of Semiconductors</i> , 2011 , 32, 114002	2.3	3
282	A new high voltage SOI LDMOS with triple RESURF structure. <i>Journal of Semiconductors</i> , 2011 , 32, 0740063	2.3	3
281	Partial-SOI high voltage P-channel LDMOS with interface accumulation holes. <i>Chinese Physics B</i> , 2011 , 20, 107101	1.2	3
280	Novel high-voltage power lateral MOSFET with adaptive buried electrodes. <i>Chinese Physics B</i> , 2012 , 21, 077101	1.2	3
279	Improvement on the breakdown voltage for silicon-on-insulator devices based on epitaxy-separation by implantation oxygen by a partial buried n + -layer. <i>Chinese Physics B</i> , 2012 , 21, 027101	1.2	3
278	High voltage SJ-LDMOS with charge-balanced pillar and N ⁺ buffer layer 2012 ,		3
277	Experimental study of the anode injection efficiency reduction of 3.3-kV-class NPT-IGBTs due to backside processes. <i>Journal of Semiconductors</i> , 2012 , 33, 024003	2.3	3
276	A new short-anoded IGBT with high emission efficiency. <i>Journal of Semiconductors</i> , 2012 , 33, 114003	2.3	3
275	A novel superjunction MOSFET with improved ruggedness under unclamped inductive switching. <i>Chinese Physics B</i> , 2012 , 21, 048502	1.2	3

274	The breakdown mechanism of a high-side pLDMOS based on a thin-layer silicon-on-insulator structure. <i>Chinese Physics B</i> , 2012 , 21, 018501	1.2	3
273	A 0.52 ppm/°C high-order temperature-compensated voltage reference. <i>Analog Integrated Circuits and Signal Processing</i> , 2010 , 62, 17-21	1.2	3
272	Optimization of the VDMOSFET structure with reduced gate charge. <i>Semiconductor Science and Technology</i> , 2007 , 22, 1033-1038	1.8	3
271	New concept for improving characteristics of high-voltage power devices by buried layers modulation effect 2006 ,		3
270	10-kV 4H-SiC Drift Step Recovery Diodes (DSRDs) for Compact High-repetition Rate Nanosecond HV Pulse Generator 2020 ,		3
269	Improved Model on Buried-Oxide Damage Induced by Total-Ionizing-Dose Effect for HV SOI LDMOS. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 2064-2070	2.9	3
268	Analytical Design and Experimental Verification of Lateral Superjunction Based on Global Region Normalization Method. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 2372-2377	2.9	3
267	Design of Hybrid Dual-Path DC-DC Converter with Wide Input Voltage Efficiency Improvement 2021 ,		3
266	Total-Ionizing-Dose Radiation-Induced Dual-Channel Leakage Current at Unclosed Edge Termination for High Voltage SOI LDMOS. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 2861-2866	2.9	3
265	Ultralow turnoff loss dual-gate SOI LIGBT with trench gate barrier and carrier stored layer. <i>Chinese Physics B</i> , 2016 , 25, 127304	1.2	3
264	Design and simulation on improving the reliability of gate oxide in SiC CDMOSFET. <i>Diamond and Related Materials</i> , 2019 , 91, 213-218	3.5	3
263	Investigation on Short-Circuit Characterization and Optimization of 3.3-kV SiC MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 184-191	2.9	3
262	A Novel SiC Asymmetric Cell Trench MOSFET With Split Gate and Integrated JBS Diode. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 9, 713-721	2.3	3
261	A Probabilistic Prediction Based Fixed-Width Booth Multiplier 2018 ,		3
260	Failure Analysis and Improvement of the Body Diode in Superjunction Power MOSFET 2018 ,		3
259	Enhancement-mode AlGaN/GaN HFET with buried-junction-barrier for breakdown improvement and threshold-voltage modulation. <i>Superlattices and Microstructures</i> , 2018 , 122, 85-92	2.8	3
258	Low Loss Insulated Gate Bipolar Transistor With Electron Injection (EI-IGBT). <i>IEEE Journal of the Electron Devices Society</i> , 2017 , 5, 275-282	2.3	2
257	A 2.6 ppm/°C 2.5 V Piece-Wise Compensated Bandgap Reference with Low Beta Bipolar. <i>Electronics (Switzerland)</i> , 2019 , 8, 555	2.6	2

256	A vertical current regulator diode with trench cathode based on double epitaxial layers for LED lighting 2015 ,		2
255	Lateral AlGaIn/GaN diode with MIS-gated hybrid anode for high-sensitivity zero-bias microwave detection. <i>Electronics Letters</i> , 2015 , 51, 1889-1891	1.1	2
254	A compact ADPLL based on symmetrical binary frequency searching with the same circuit. <i>International Journal of Electronics</i> , 2015 , 102, 462-475	1.2	2
253	Modeling the Influence of the Acceptor-Type Trap on the 2DEG Density for GaN MIS-HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 2290-2296	2.9	2
252	Non-Simultaneous Triggering Induced Failure of CS-MCT Under Repetitive High-Current Pulse Condition. <i>IEEE Transactions on Device and Materials Reliability</i> , 2020 , 20, 214-220	1.6	2
251	220 GHz wideband integrated receiver front end based on planar Schottky diodes. <i>Microwave and Optical Technology Letters</i> , 2020 , 62, 2737-2746	1.2	2
250	An AlGaIn/GaN current regulating diode 2017 ,		2
249	A GaN enhancement-mode reverse blocking MISHEMT with MIS field-effect drain for bidirectional switch. <i>Journal of Computational Electronics</i> , 2018 , 17, 238-245	1.8	2
248	A 0.3V/1.2V ultra-low input voltage, reconfigurable switched-capacitor DC-DC converter for energy harvesting system 2016 ,		2
247	A low turnoff loss SOI LIGBT with p-buried layer and double gates 2016 ,		2
246	Impact of interface traps on switching behavior of normally-OFF AlGaIn/GaN MOS-HEMTs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 328-331		2
245	Investigation on the device geometry-dependent reverse recovery characteristic of AlGaIn/GaN lateral field-effect rectifier (L-FER). <i>Superlattices and Microstructures</i> , 2018 , 120, 605-610	2.8	2
244	A Novel 3300V Trench IGBT with Hole Extraction Structure for Low Power Loss 2019 ,		2
243	A High Accuracy Weak Voltage LED Analog Dimming Method. <i>IEEE Access</i> , 2019 , 7, 172362-172373	3.5	2
242	Numerical Analysis of Impact of Shield Gate on Trench IGBT and CSTBT 2019 ,		2
241	A High-Efficiency 220 GHz Doubler Based on the Planar Schottky Varactor Diode. <i>Journal of Electronic Materials</i> , 2019 , 48, 3603-3611	1.9	2
240	. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2019 , 7, 1440-1448	5.6	2
239	A High-Accuracy AlGaIn/GaN Reverse Blocking CRD (RB-CRD) with Hybrid Trench Cathode. <i>Nanoscale Research Letters</i> , 2019 , 14, 23	5	2

- 238 A 700 V narrow channel nJFET with low pinch-off voltage and suppressed drain-induced barrier lowering effect. *Superlattices and Microstructures*, **2014**, 75, 576-585 2.8 2
- 237 Bypass anode lateral IGBT on SOI for snapback suppression. *IEICE Electronics Express*, **2014**, 11, 20140470-20140470 2.5 2
- 236 A low-power on-chip LDO with advanced reference buffer. *IEICE Electronics Express*, **2014**, 11, 20140824-20140824 2.5 2
- 235 Split compensation for inverter-based two-stage amplifier. *Microelectronics Journal*, **2013**, 44, 683-687 1.8 2
- 234 Investigation of a latch-up immune silicon controlled rectifier for robust ESD application **2017**, 2
- 233 High holding voltage SCR for robust electrostatic discharge protection. *Chinese Physics B*, **2017**, 26, 077304 2.4 2
- 232 A rugged 650 V SOI-based high-voltage half-bridge IGBT gate driver IC for motor drive applications. *International Journal of Electronics*, **2015**, 102, 755-764 1.2 2
- 231 A miniature high-efficiency fully digital adaptive voltage scaling buck converter. *International Journal of Electronics*, **2015**, 102, 1520-1534 1.2 2
- 230 A low specific on-resistance SOI LDMOS with a novel junction field plate. *Chinese Physics B*, **2014**, 23, 077306 1.2 2
- 229 A novel Triple-RESURF SON LDMOS and its analytical model **2014**, 2
- 228 A 800 V dual conduction paths segmented anode LIGBT with low specific on-resistance and small shift voltage. *Journal of Semiconductors*, **2014**, 35, 054004 2.3 2
- 227 Modelling and analysis of a high-performance Class D audio amplifier using unipolar pulse-width-modulation. *International Journal of Electronics*, **2012**, 99, 163-177 1.2 2
- 226 Analysis and reduction of the gate forward leakage current in AlGaN/GaN HEMTs employing energy-band modulation technology. *Solid-State Electronics*, **2013**, 80, 76-80 1.7 2
- 225 A Low Specific on-Resistance SOI Trench MOSFET with a Non-Depleted Embedded p-Island. *Chinese Physics Letters*, **2013**, 30, 078501 1.8 2
- 224 Analysis of the dV/dt effect on an IGBT gate circuit in IPM. *Journal of Semiconductors*, **2013**, 34, 045001 2.3 2
- 223 Analysis on the positive dependence of channel length on ESD failure current of a GGNMOS in a 5 V CMOS. *Journal of Semiconductors*, **2013**, 34, 024004 2.3 2
- 222 **2011**, 2
- 221 A novel TFS-IGBT with a super junction floating layer. *Journal of Semiconductors*, **2010**, 31, 114008 2.3 2

220	An enhanced double current limit technique used in high power BUCK converter 2009 ,		2
219	The effect of the surface recombination on current gain for 4H-SiC BJT 2009 ,		2
218	A novel planar vertical double-diffused metal-oxide-semiconductor field-effect transistor with inhomogeneous floating islands. <i>Chinese Physics B</i> , 2011 , 20, 128501	1.2	2
217	High voltage SOI LDMOS with a compound buried layer. <i>Journal of Semiconductors</i> , 2012 , 33, 104003	2.3	2
216	Embedded current amplifier compensation for large-capacitive-load low-power two-stage amplifier 2012 ,		2
215	A short-contacted double anodes IGBT 2012 ,		2
214	Super junction LDMOS technologies for power integrated circuits 2012 ,		2
213	A Novel Controllable Hybrid-Anode AlGaN/GaN Field-Effect Rectifier with Low Operation Voltage. <i>Chinese Physics Letters</i> , 2012 , 29, 107202	1.8	2
212	Design of novel bootstrap driver used in high power BUCK converter 2009 ,		2
211	Characteristic analysis of switching voltage power spectra under the mode of random carrier-frequency modulation. <i>COMPEL - the International Journal for Computation and Mathematics in Electrical and Electronic Engineering</i> , 2010 , 29, 484-494	0.7	2
210	A new MOS gate thyristor—the single-gate emitter controlled thyristor (SECT). <i>Solid-State Electronics</i> , 1997 , 41, 1233-1239	1.7	2
209	High breakdown voltage 4H-SiC Schottky Barrier Diodes with floating metal rings for MMIC applications 2006 ,		2
208	A novel improved PSM mode in DC-DC converter based on energy balance		2
207	Design and Fabrication of a High Performance LDMOSFET with Step Doped Drift Region on Bonded SOI Wafers 2006 ,		2
206	A dual complex pole-zero cancellation frequency compensation with gain-enhanced stage for three-stage amplifier. <i>Analog Integrated Circuits and Signal Processing</i> , 2006 , 48, 175-180	1.2	2
205	Analysis of Short-Circuit Behavior for SiC MOSFETs with Various Circuit Characteristics 2020 ,		2
204	Theoretical and Experimental Study on AlGaN/GaN Schottky Barrier Diode on Si Substrate with Double-Heterojunction. <i>Nanoscale Research Letters</i> , 2020 , 15, 149	5	2
203	Theory and optimization of the power super junction device. <i>Scientia Sinica: Physica, Mechanica Et Astronomica</i> , 2016 , 46, 107302	1.5	2

202	4H-SiC trench MOSFET with an integrated Schottky barrier diode and L-shaped P+ shielding region. <i>Journal of Semiconductors</i> , 2020 , 41, 102801	2.3	2
201	Wideband Dual-Circular-Polarization Antenna with High Isolation for Millimeter-Wave Wireless Communications. <i>IEEE Transactions on Antennas and Propagation</i> , 2021 , 1-1	4.9	2
200	An analytical model on the gate control capability in p-GaN Gate AlGaN/GaN high-electron-mobility transistors considering buffer acceptor traps. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 095107	3	2
199	An Improved Nonlinear Circuit Model for GaAs Gunn Diode in W-Band Oscillator. <i>IEICE Transactions on Electronics</i> , 2009 , E92-C, 1490-1495	0.4	2
198	An Ultralow Loss N-channel RB-IGBT with P-drift Region 2020 ,		2
197	A review of high-voltage integrated power device for AC/DC switching application. <i>Microelectronic Engineering</i> , 2020 , 232, 111416	2.5	2
196	Modeling the Displacement Damage on Trigger Current of Anode-Short MOS-Controlled Thyristor. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 1043-1049	2.3	2
195	A Low Loss and On-State Voltage Superjunction IGBT with Depletion Trench 2020 ,		2
194	Investigating the Failure Mechanism of Short-Circuit Tests in 1.2-kV SiC JBS-Integrated MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 4027-4032	2.9	2
193	Low Switching Loss and EMI Noise IGBT With Self-Adaptive Hole-Extracting Path. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 2572-2576	2.9	2
192	Modeling of a triple reduced surface field silicon-on-insulator lateral double-diffused metal-oxide-semiconductor field-effect transistor with low on-state resistance. <i>Chinese Physics B</i> , 2016 , 25, 027305	1.2	2
191	NBTI of buried oxide layer induced degradation for thin layer SOI field pLDMOS 2016 ,		2
190	An Improved Composite JTE Termination Technique for Ultrahigh Voltage 4H-SiC Power Devices 2019 ,		2
189	Design and Characteristics of an Etching Field Limiting Ring for 10kV SiC Power Device 2019 ,		2
188	A High-Precision Bandgap Voltage Reference with Automatic Curvature-Compensation Technique. <i>Journal of Circuits, Systems and Computers</i> , 2019 , 28, 1950214	0.9	2
187	A novel GaN-based lateral SBD with a TUG-AlGaN/GaN heterojunction. <i>Superlattices and Microstructures</i> , 2019 , 126, 174-180	2.8	2
186	A Time-Efficient Automatic Circuit Approximation Method. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2020 , 67, 3047-3055	3.9	2
185	Experiments of a Lateral Power Device With Complementary Homogenization Field Structure. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	2

184	Wide stopband millimeter/terahertz lowpass filter using improved split ring resonator. <i>Journal of Electromagnetic Waves and Applications</i> , 2018 , 32, 579-590	1.3	2
183	Simulation of a high-performance enhancement-mode HFET with back-to-back graded AlGaIn layers. <i>Science China Information Sciences</i> , 2018 , 62, 1	3.4	2
182	High-Voltage SOI Deep Trench LDMOS with Quasi Vertical Super Junction Structure 2018 ,		2
181	Shielded Gate SiC Trench Power MOSFET with Ultra-Low Switching Loss. <i>Materials Science Forum</i> , 2018 , 924, 765-769	0.4	2
180	A novel enhancement-mode GaN vertical MOSFET with double hetero-junction for threshold voltage modulation. <i>Superlattices and Microstructures</i> , 2018 , 123, 297-305	2.8	2
179	Analytical Model and Mechanism of Homogenization Field for Lateral Power Devices. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 3956-3962	2.9	2
178	A Lateral AlGaIn/GaN Diode with MIS-Gated Hybrid Anode for Ultra-Low Turn-On and High Breakdown Voltage. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, S3056-S3059	2	1
177	4.5kV Insulated Gate Triggered Thyristor (IGTT) with High di/dt Characteristics for Pulse Power Applications 2019 ,		1
176	Silicon carbide bipolar junction transistor with novel emitter field plate design for high current gain and reliability. <i>Semiconductor Science and Technology</i> , 2019 , 34, 045001	1.8	1
175	A simulation study of the micro-grooved electrode structure for back-contact back-junction silicon solar cell. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 014301	1.4	1
174	Ultralow specific on-resistance high voltage trench SOI LDMOS with enhanced RESURF effect. <i>Journal of Semiconductors</i> , 2015 , 36, 024010	2.3	1
173	A semi-superjunction MOSFET with P-type Bottom Assist Layer. <i>Superlattices and Microstructures</i> , 2015 , 83, 745-754	2.8	1
172	Ultralow Specific on-Resistance Trench MOSFET with a U-Shaped Extended Gate. <i>Chinese Physics Letters</i> , 2015 , 32, 068501	1.8	1
171	A novel high figure-of-merit SOI SJ LDMOS with ultra-strong charge accumulation effect. <i>Journal of Semiconductors</i> , 2015 , 36, 034007	2.3	1
170	Mix-mode forward-biased diode with low clamping voltage for robust ESD applications. <i>Electronics Letters</i> , 2020 , 56, 398-400	1.1	1
169	A Novel Snapback-Free Reverse-Conducting IGBT with Si/SiC Heterojunction 2020 ,		1
168	Analysis of Welding Pad for Terahertz Hybrid Integrated Mixer. <i>IEEE Access</i> , 2020 , 8, 22506-22514	3.5	1
167	High performance floating p-well carrier stored trench bipolar transistor with L-shaped shield gates. <i>Electronics Letters</i> , 2020 , 56, 205-207	1.1	1

166	Influence of the filling holes on the high temperature characteristics of deep trench superjunction MOSFET 2017 ,		1
165	420 GHz subharmonic mixer based on heterogeneous integrated Schottky diode. <i>IEICE Electronics Express</i> , 2017 , 14, 20170459-20170459	0.5	1
164	0.3 VT/1.1 kV AlGaIn/GaN lateral power diode with MIS-gated hybrid anode on silicon substrate 2016 ,		1
163	Cost-effective mask-sharing technology for SOI LIGBT and PLDMOS. <i>Superlattices and Microstructures</i> , 2016 , 92, 359-365	2.8	1
162	200-V High-side thick-layer SOI field p-channel LDMOS with multiple field plates. <i>Superlattices and Microstructures</i> , 2016 , 90, 141-147	2.8	1
161	Dynamic stability analysis based on state-space model and Lyapunov stability criterion for SiC-MOS and Si-IGBT switching 2018 ,		1
160	Novel AlGaIn/GaN SBDs with nanoscale multi-channel for gradient 2DEG modulation 2018 ,		1
159	A High-reliability Half-Bridge GaN FET Gate Driver with Advanced Floating Bias Control Techniques 2019 ,		1
158	A wide-bandwidth PSR-enhanced low-dropout regulator using a bandpass feedforward supply ripple rejection circuit. <i>Analog Integrated Circuits and Signal Processing</i> , 2014 , 80, 221-232	1.2	1
157	Enhancing the robustness of the equipotential ring of edge termination for 4.5KV IGBT by introducing a Partial N layer. <i>Superlattices and Microstructures</i> , 2014 , 65, 124-133	2.8	1
156	Embedded advanced capacitor multiplier compensation for two-stage amplifier with large capacitive loads 2013 ,		1
155	ESD characterization of a 190V LIGBT SOI ESD power clamp structure for plasma display panel applications. <i>Microelectronics Reliability</i> , 2013 , 53, 687-693	1.2	1
154	A robust and area-efficient guard ring edge termination technique for 4H-SiC power MOSFETs. <i>Materials Science in Semiconductor Processing</i> , 2017 , 68, 108-113	4.3	1
153	Lateral AlGaIn/GaN power diode with MIS-Gated hybrid anode for ultra-low turn-on voltage and high breakdown voltage 2017 ,		1
152	A high-precision voltage regulator with dynamic load technique and overcurrent protection 2017 ,		1
151	A 3.7ppm/°C piece-wise compensated bandgap reference 2017 ,		1
150	Variable on time controlled buck converter for DVS applications 2017 ,		1
149	High voltage driver IC with improved immunity to di/dt induced substrate noise. <i>IEICE Electronics Express</i> , 2015 , 12, 20150189-20150189	0.5	1

148	Effect of post oxidation annealing in nitric oxide on interface properties of 4H-SiC/SiO ₂ after high temperature oxidation. <i>Journal of Semiconductors</i> , 2015 , 36, 094003	2.3	1
147	Design, fabrication and characterization of mesa combined with JTE termination for high-voltage 4H-SiC PiN diodes. <i>Superlattices and Microstructures</i> , 2015 , 88, 167-173	2.8	1
146	High performance AlGaN/GaN power diode with edge-terminated hybrid anode 2014 ,		1
145	Experimental and theoretical study of an improved breakdown voltage SOI LDMOS with a reduced cell pitch. <i>Journal of Semiconductors</i> , 2014 , 35, 024007	2.3	1
144	A novel SOI high-voltage SJ-pLDMOS based on self-adaptive charge balance. <i>Journal of Semiconductors</i> , 2014 , 35, 024004	2.3	1
143	High current gain 4H-SiC BJT for limiting surface states effect 2014 ,		1
142	High Voltage SiC JBS Diodes with Multiple Zone Junction Termination Extension Using Single Etching Step. <i>Materials Science Forum</i> , 2014 , 778-780, 808-811	0.4	1
141	A simple method to design the single-mask multi-zone junction termination extension for high-voltage IGBT 2012 ,		1
140	High-voltage thin layer SOI technology for negative power supply 2012 ,		1
139	A Snapback Suppressed Reverse Conducting IGBT with Oxide Trench Collector 2012 ,		1
138	Innovative Buried Layer Rectifier with 0.1V ultralow forward conduction voltage 2012 ,		1
137	A dual-gate and dielectric-inserted lateral trench insulated gate bipolar transistor on a silicon-on-insulator substrate. <i>Chinese Physics B</i> , 2013 , 22, 077309	1.2	1
136	A low on-resistance buried current path SOI p-channel LDMOS compatible with n-channel LDMOS. <i>Chinese Physics B</i> , 2013 , 22, 067306	1.2	1
135	A high voltage SOI pLDMOS with a partial interface equipotential floating buried layer. <i>Journal of Semiconductors</i> , 2013 , 34, 074009	2.3	1
134	A Novel Silicon-on-Insulator Super-Junction Lateral-Double-Diffused Metal-Oxide-Semiconductor Transistor with T-Dual Dielectric Buried Layers. <i>Chinese Physics Letters</i> , 2013 , 30, 127102	1.8	1
133	Fluorine-plasma surface treatment for gate forward leakage current reduction in AlGaN/GaN HEMTs. <i>Journal of Semiconductors</i> , 2013 , 34, 024003	2.3	1
132	A high performance carrier stored trench bipolar transistor with a field-modified P-base region. <i>Journal of Semiconductors</i> , 2013 , 34, 044008	2.3	1
131	A novel ESD protection structure for output pads. <i>Journal of Semiconductors</i> , 2013 , 34, 114016	2.3	1

- 130 ESD performance of LDMOS with source-bulk layout structure optimization. *Journal of Semiconductors*, **2013**, 34, 124003 2.3 1
- 129 A high voltage silicon-on-insulator lateral insulated gate bipolar transistor with a reduced cell-pitch. *Chinese Physics B*, **2013**, 22, 027303 1.2 1
- 128 A 1.74 ppm/°C, high PSRR bandgap reference with fast start-up **2011**, 1
- 127 Breakdown voltage enhancement for power AlGaIn/GaN HEMTs with Air-bridge Field Plate **2011**, 1
- 126 A simple and effective ESD protection structure for high-voltage-tolerant I/O pad **2010**, 1
- 125 An analytical model for high voltage thin-film Silicon On Insulator RESURF devices **2010**, 1
- 124 A novel hybrid-anode AlGaIn/GaN field-effect rectifier with low operation voltage **2010**, 1
- 123 A high-performance bandgap reference with advanced curvature-compensation **2011**, 1
- 122 A novel lateral IGBT with a controlled anode for on-off-state loss trade-off improvement. *Journal of Semiconductors*, **2011**, 32, 074005 2.3 1
- 121 A digitally controlled PWM/PSM dual-mode DC/DC converter. *Journal of Semiconductors*, **2011**, 32, 115007 2.3 1
- 120 Novel SOI double-gate MOSFET with a P-type buried layer. *Journal of Semiconductors*, **2012**, 33, 054006 2.3 1
- 119 Fabrication characteristics of 1.2kV SiC junction barrier schottky rectifiers with etched implant junction termination extension **2012**, 1
- 118 Universal trench design method for a high-voltage SOI trench LDMOS. *Journal of Semiconductors*, **2012**, 33, 074006 2.3 1
- 117 Monolithic integration of an AlGaIn/GaN metal-insulator field-effect transistor with an ultra-low voltage-drop diode for self-protection. *Chinese Physics B*, **2012**, 21, 087305 1.2 1
- 116 New Lateral IGBT on partial membrane **2008**, 1
- 115 Improved performance of 3D tri-gate 4H-SiC MESFETs with recessed drift region **2008**, 1
- 114 A novel high voltage LDMOS for HVIC with the multiple step shaped equipotential rings. *Solid-State Electronics*, **2007**, 51, 394-397 1.7 1
- 113 An Ultra-Low Gate Charge Shield Gate MOSFET with Pinch-Off Region and Schottky Contact **2020**, 1

112	Cut-Off Degradation of Output Current Induced by High Fluence Neutron Radiation in High-Voltage Silicon-on-Insulator Lateral Double-Diffused MOSFET. <i>IEEE Electron Device Letters</i> , 2022 , 43, 108-111	4.4	1
111	Review of technologies for high-voltage integrated circuits. <i>Tsinghua Science and Technology</i> , 2022 , 27, 495-511	3.4	1
110	A novel GaN vertical junction field-effect transistor with intrinsic reverse conduction capability and kilo-volt breakdown voltage. <i>Semiconductor Science and Technology</i> , 2021 , 36, 024004	1.8	1
109	A Novel SiC MOSFET With Embedded Auto-Adjust JFET With Improved Short Circuit Performance. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	1
108	A New Driving Topology for DC Motor to Suppress Kickback Voltage. <i>Lecture Notes in Electrical Engineering</i> , 2011 , 1001-1013	0.2	1
107	Experimental study and characterization of an ultrahigh-voltage Ni/4H ₂ SiC junction barrier Schottky rectifier with near ideal performances. <i>Superlattices and Microstructures</i> , 2020 , 138, 106381	2.8	1
106	Prototype of Edge Computing IPM with Hardware Artificial Neural Network Soft Sensor and Controller for Parallel Connected IGBT Current Distribution 2020 ,		1
105	Different JFET Designs on Conduction and Short-Circuit Capability for 3.3 kV Planar-Gate Silicon Carbide MOSFETs. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 841-845	2.3	1
104	Design and Anaysis of The Average Current-Detection Method for Wide Input Voltage Range Constant-Current Lighting LED Driver 2020 ,		1
103	Ionization Damage Effects of Pulse Discharge Circuit Switched by Anode-Short MOS-Controlled Thyristor. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 1096-1104	2.3	1
102	Avalanche Ruggedness Assessment of 1.2kV 45m ² Asymmetric Trench SiC MOSFETs. <i>Materials Science Forum</i> , 2020 , 1004, 837-842	0.4	1
101	Evaluation of an Effective DC Solid State Circuit Breaker Based on CS-MCT 2021 ,		1
100	. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 1542-1549	2.9	1
99	An Optimal Designed Compensator for PSR Flyback Converters Based on Genetic Algorithm 2019 ,		1
98	2019 ,		1
97	1.1 THz tenth harmonic mixer based on planar GaAs Schottky diode. <i>IET Microwaves, Antennas and Propagation</i> , 2019 , 13, 1799-1803	1.6	1
96	High Reliability GaN FET Gate Drivers for Next-generation Power Electronics Technology 2019 ,		1
95	HEMT Small-Signal Modelling for Voltage-Controlled Attenuator Applications 2019 ,		1

94	The Minimum Specific on-Resistance of Semi-SJ Device. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 598-604	2.9	1
93	Influence of the Acceptor-Type Trap on the Threshold Voltage of the Short-Channel GaN MOS-HEMT. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 9, 606-611	2.3	1
92	A low turn-on voltage AlGaN/GaN lateral field-effect rectifier compatible with p-GaN gate HEMT technology. <i>Semiconductor Science and Technology</i> , 2021 , 36, 034004	1.8	1
91	High-voltage trench-gate hole-gas enhancement-mode HEMT with multi-conduction channels. <i>Science China Information Sciences</i> , 2018 , 61, 1	3.4	1
90	A Fast-Response BUCK Converter with Adaptive Detect and Transient Enhancement Techniques 2018 ,		1
89	High performance bidirectional IGBT with sandwich super junction structure 2018 ,		1
88	A Near Ideal Edge Termination Technique for Ultrahigh-Voltage 4H-SiC Devices with Multi-Zone Gradient Field Limiting Ring 2018 ,		1
87	Single-Event Effect Hardened VDMOS Device with Hole Bypass Structure 2018 ,		1
86	A Superjunction MOSFET with Ultralow Reverse Recovery Charge and Low Switching Losses. <i>Journal of Electronic Materials</i> , 2021 , 50, 6297-6306	1.9	1
85	Experimental Realization of Ultralow ON-Resistance LDMOS With Optimized Layout. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 4168-4172	2.9	1
84	Deep Understanding of Negative Gate Voltage Restriction for SiC mosfet Under Wide Temperature Range. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 8622-8627	7.2	1
83	Seamless Mode-Switch Control Scheme for Primary Side Regulation Flyback With Capacitorless Self-Adaptive Startup. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 9668-9677	7.2	1
82	Simulation Study of a High Gate-to-Source ESD Robustness Power p-GaN HEMT With Self-Triggered Discharging Channel. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 4536-4542	2.9	1
81	Analyses and Experiments of Ultralow Specific On-resistance LDMOS with Integrated Diodes. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 1-1	2.3	1
80	Experiments of Homogenization Field LDMOS With Trench-Stopped Depletion. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-6	2.9	1
79	Investigation of Failure Mechanisms of 1200V Rated Trench SiC MOSFETs under Repetitive Avalanche Stress. <i>IEEE Transactions on Power Electronics</i> , 2022 , 1-1	7.2	1
78	Investigation on Total-Ionizing-Dose Radiation Response for 700V Double-RESURF SOI LDMOS. <i>IEEE Transactions on Nuclear Science</i> , 2022 , 1-1	1.7	1
77	650 V Super-Junction Insulated Gate Bipolar Transistor Based on 45 μm Ultrathin Wafer Technology. <i>IEEE Electron Device Letters</i> , 2022 , 43, 592-595	4.4	1

76	Non-resonant soft-switching technique with linear current on switching cycle time-scale for switched-capacitor DC-DC converters. <i>IET Power Electronics</i> , 2022 , 15, 287-305	2.2	1
75	Numerical Analysis for a P-Drift Region N-IGBT With Enhanced Dynamic Electric Field Modulation Effect. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-6	2.9	1
74	Development of a Wideband 220-GHz Subharmonic Mixer Based on GaAs Monolithic Integration Technology. <i>IEEE Access</i> , 2020 , 8, 31214-31226	3.5	0
73	. <i>IEEE Transactions on Power Electronics</i> , 2016 , 31, 4499-4508	7.2	0
72	Reverse conducting lateral insulated-gate bipolar transistors with a non-local band-to-band tunnelling junction. <i>Micro and Nano Letters</i> , 2014 , 9, 544-547	0.9	0
71	A novel high performance TFS SJ IGBT with a buried oxide layer. <i>Chinese Physics B</i> , 2014 , 23, 088504	1.2	0
70	A 2.65 W high-fidelity filterless class D audio amplifier using multiple loop filters. <i>Analog Integrated Circuits and Signal Processing</i> , 2013 , 74, 417-423	1.2	0
69	Output characteristics analysis for n-buried-PSOI sandwiched RF power LDMOS. <i>COMPEL - the International Journal for Computation and Mathematics in Electrical and Electronic Engineering</i> , 2010 , 29, 528-535	0.7	0
68	A Low-Power Ultra-Fast Capacitor-Less LDO with Advanced Dynamic Push-Pull Techniques. <i>International Federation for Information Processing</i> , 2012 , 34-51		0
67	A Novel Trench-Gated Vertical GaN Transistor With Dual-Current-Aperture by Electric-field Engineering for High Breakdown Voltage. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-7	2.9	0
66	Ultrathin barrier AlGaN/GaN hybrid-anode-diode with MOCVD in-situ Si ₃ N ₄ -cap and LPCVD-Si ₃ N ₄ bilayer passivation stack for dynamic characteristic improvement. <i>Electronics Letters</i> , 2020 , 56, 789-791	1.1	0
65	High voltage trench insulated gate bipolar transistor with MOS structure for self-adjustable hole extraction. <i>Semiconductor Science and Technology</i> , 2020 , 35, 11LT01	1.8	0
64	Mechanisms and characteristics of a low-loss split gate trench MOSFET with shield layer. <i>Microelectronics Journal</i> , 2021 , 118, 105310	1.8	0
63	Analysis of Energy Loss in GaN E-mode Devices under UIS Stresses. <i>IEEE Transactions on Power Electronics</i> , 2021 , 1-1	7.2	0
62	A compact model of shield-gate trench MOSFET based on BSIM4. <i>Wuli Xuebao/Acta Physica Sinica</i> , 2020 , 69, 177103	0.6	0
61	A Lateral Regulator Diode with Field Plates for Light-Emitting-Diode Lighting. <i>Chinese Physics Letters</i> , 2016 , 33, 097101	1.8	0
60	PB-SON RFLDMOS characteristics analysis. <i>COMPEL - the International Journal for Computation and Mathematics in Electrical and Electronic Engineering</i> , 2010 , 29, 522-527	0.7	0
59	High Trigger Current NPN Transistor With Excellent Double-Snapback Performance for High-Voltage Output ESD Protection. <i>IEEE Electron Device Letters</i> , 2020 , 41, 453-456	4.4	0

58	Voltage Coupling Enhancement for Transient Gate Overvoltage Suppression of Insulated Gate Trigger Thyristor in Ultrahigh di/dt Pulse Applications. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 3346-3353	7.2	o
57	A Novel Synchronous Rectification with Directly Frequency Tracking for Automotive Alternator. <i>IEEE Transactions on Industrial Electronics</i> , 2021 , 1-1	8.9	o
56	Investigation on 4H SiC MOSFET with three-section edge termination. <i>Superlattices and Microstructures</i> , 2018 , 124, 139-144	2.8	o
55	Low Loss and Low EMI Noise CSTBT With Split Gate and Recessed Emitter Trench. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 9, 704-712	2.3	o
54	A Fast-Transient Capacitor-Less LDO With Dual Paths Active-Frequency Compensation Scheme. <i>IEEE Transactions on Power Electronics</i> , 2022 , 1-1	7.2	o
53	Reverse Blocking p-GaN Gate HEMTs with Multi-column p-GaN/Schottky Alternate-island Drain. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	o
52	A variable nanotrench structure for electric field modulation in AlGaIn/GaN devices. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SBBD02	1.4	
51	Novel substrate trigger SCR-LDMOS stacking structure for high-voltage ESD protection application. <i>Chinese Physics B</i> , 2015 , 24, 047303	1.2	
50	Operation mechanism and performance optimization for a novel ultralow loss SOI LIGBT with high current capability. <i>Semiconductor Science and Technology</i> , 2020 , 35, 045005	1.8	
49	A novel AlGaIn/GaN hybrid-anode current regulating diode (CRD) with step-graded Schottky-Ohmic cathode. <i>Superlattices and Microstructures</i> , 2018 , 123, 52-59	2.8	
48	A novel progressive trigger method of di/dt control for MOSFET. <i>IEICE Electronics Express</i> , 2016 , 13, 20151006-20151006	1.9	
47	High current gain 4H-SiC bipolar junction transistor. <i>Journal of Semiconductors</i> , 2016 , 37, 044005	2.3	
46	Back gate induced breakdown mechanisms for thin layer SOI field P-channel LDMOS. <i>Superlattices and Microstructures</i> , 2016 , 89, 216-224	2.8	
45	An Integrated Transient Enhancement Circuit Suitable for Buck Converter With Large Output Capacitor. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2019 , 66, 1743-1747	3.5	
44	A fast-transient on-chip LDO with advanced dynamic biasing circuit. <i>IEICE Electronics Express</i> , 2014 , 11, 20140690-20140690	0.5	
43	A reliability improved synchronous boost converter with spike suppression circuit. <i>IEICE Electronics Express</i> , 2015 , 12, 20150916-20150916	0.5	
42	Observation of a Current Plateau in the Transfer Characteristics of InGaIn/AlGaIn/AlN/GaN Heterojunction Field Effect Transistors. <i>Chinese Physics Letters</i> , 2015 , 32, 127301	1.8	
41	Low Loss Intelligent Power Module with TFS-IGBTs and SiC SBDs. <i>IEICE Transactions on Electronics</i> , 2015 , E98.C, 981-983	0.4	

- 40 Design of low-power hybrid digital pulse width modulator with piecewise calibration scheme. *International Journal of Electronics*, **2015**, 102, 2127-2141 1.2
- 39 Increasing substrate resistance to improve the turn-on uniformity of a high-voltage multi-finger GG-nLDMOS. *Journal of Semiconductors*, **2013**, 34, 014006 2.3
- 38 Low on-resistance high-voltage lateral double-diffused metal oxide semiconductor with a buried improved super-junction layer. *Chinese Physics B*, **2014**, 23, 038503 1.2
- 37 A fast-transient high-PSR output-capacitor-free low-dropout regulator for low-power embedded systems. *Analog Integrated Circuits and Signal Processing*, **2014**, 81, 443-451 1.2
- 36 A novel NLDMOS with a high ballast resistance for ESD protection. *Journal of Semiconductors*, **2014**, 35, 024005 2.3
- 35 A high voltage Bi-CMOS compatible buffer super-junction LDMOS with an N-type buried layer. *Journal of Semiconductors*, **2014**, 35, 014009 2.3
- 34 Design of low noise class D amplifiers using an integrated filter. *Journal of Semiconductors*, **2012**, 33, 115002 2.3
- 33 NOVEL HIGH VOLTAGE SILICON-ON-INSULATOR DEVICE WITH COMPOSITE DIELECTRIC BURIED LAYER. *Journal of Circuits, Systems and Computers*, **2013**, 22, 1340029 0.9
- 32 Analysis of OFF-state and ON-state performance in a silicon-on-insulator power MOSFET with a low-kdielectric trench. *Journal of Semiconductors*, **2013**, 34, 074006 2.3
- 31 Eliminating the floating-body effects in a novel CMOS-compatible thin-SOI LDMOS. *Journal of Semiconductors*, **2013**, 34, 094005 2.3
- 30 Analytical model for high-voltage SOI device with composite-kdielectric buried layer. *Journal of Semiconductors*, **2013**, 34, 094008 2.3
- 29 Ultra-low specific on-resistance vertical double-diffused metaloxide semiconductor with a high-kdielectric-filled extended trench. *Chinese Physics B*, **2013**, 22, 027305 1.2
- 28 A novel high voltage LIGBT with an n-region in p-substrate. *Journal of Semiconductors*, **2011**, 32, 114003 2.3
- 27 A thick SOI UVLD LIGBT on partial membrane. *Journal of Semiconductors*, **2011**, 32, 024008 2.3
- 26 Super junction LDMOS with enhanced dielectric layer electric field for high breakdown voltage. *Journal of Semiconductors*, **2011**, 32, 024002 2.3
- 25 ESD robustness studies on the double snapback characteristics of an LDMOS with an embedded SCR. *Journal of Semiconductors*, **2011**, 32, 094002 2.3
- 24 Complementary charge islands structure for a high voltage device of partial-SOI. *Journal of Semiconductors*, **2011**, 32, 014003 2.3
- 23 Design of Class D Amplifiers Using Zero Crossing Auto Gain Control. *Applied Mechanics and Materials*, **2012**, 198-199, 1157-1161 0.3

22	Analysis of the breakdown mechanism for an ultra high voltage high-side thin layer silicon-on-insulator p-channel lateral double-diffused metal-oxide semiconductor. <i>Chinese Physics B</i> , 2012 , 21, 037305	1.2
21	A high linearity current mode multiplier/divider with a wide dynamic range. <i>Journal of Semiconductors</i> , 2012 , 33, 125003	2.3
20	Impact of parasitic resistance on the ESD robustness of high-voltage devices. <i>Journal of Semiconductors</i> , 2012 , 33, 014005	2.3
19	Novel 4H-SiC BJT utilizing floating buried layer in base for high current gain, high current gain stability and high breakdown voltage. <i>COMPEL - the International Journal for Computation and Mathematics in Electrical and Electronic Engineering</i> , 2010 , 29, 515-521	0.7
18	Influence of the minority carrier extracted by the base electrode on current gain of bipolar power transistors. <i>Solid-State Electronics</i> , 2006 , 50, 480-488	1.7
17	The Superjunction Device with Optimized Process Window of Breakdown Voltage	
16	Barrier Lowering-Induced Capacitance Increase of Short-Channel Power p-GaN HEMTs at High Temperature. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-5	2.9
15	Enhanced Reverse Recovery Performance in Superjunction MOSFET with Reduced Hole-Barrier. <i>ECS Journal of Solid State Science and Technology</i> , 2022 , 11, 015002	2
14	Reverse Blocking GaN High Electron Mobility Transistors with Stepped P-GaN Drain. <i>ECS Journal of Solid State Science and Technology</i> , 2022 , 11, 025002	2
13	Temperature Dependence of Pulsed Power Performance of Insulated Gate Trigger Thyristor. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-8	2.9
12	Characterization and Fabrication of the CFM-JTE for 4H-SiC Power Device with High-Efficiency Protection and Increased JTE Dose Tolerance Window. <i>Nanoscale Research Letters</i> , 2020 , 15, 211	5
11	Investigation and Modeling of the Avalanche Failure Mechanism of 1.2-kV 4H-SiC J MOS. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 6313-6320	2.9
10	Investigation of breakdown voltage degradation in low-voltage narrow gate trench MOSFET by edge termination optimization. <i>Semiconductor Science and Technology</i> , 2021 , 36, 115014	1.8
9	High-Performance 110-140-GHz Broadband Fixed-Tuned Varistor Mode Schottky Diode Tripler Incorporating CMRC for Submillimeter-Wave Applications. <i>IEICE Transactions on Electronics</i> , 2011 , E94-C, 1605-1610	0.4
8	The research on 220-GHz signal detecting system. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , 2020 , 33, e2655	1
7	An Error Amplifier With a Low Power Multi-Mode Voltage Clamper for Transient Enhancement and High Reliability. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2020 , 67, 4075-4084	3.9
6	On instabilities and thermal post-buckling of the electrically annular system coupled with shape-memory alloy fibers. <i>Mechanics Based Design of Structures and Machines</i> , 1-21	1.7
5	A 0.85 V, 4.9 ppm/°C inherent temperature compensated voltage reference with 82 dB PSRR. <i>IEICE Electronics Express</i> , 2018 , 15, 20180957-20180957	0.5

4	Injection enhanced SiC planar gate IGBT with partial Schottky contact emitter. <i>Materials Science in Semiconductor Processing</i> , 2021 , 134, 106026	4.3
3	A High-Performance 330-GHz Subharmonic Mixer Using Schottky Diodes. <i>IEEE Microwave and Wireless Components Letters</i> , 2022 , 1-4	2.6
2	A Novel Gate-to-Source ESD Protection Clamp for GaN HEMT. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-6	2.9
1	A Gradient Doped Integrated JFET With Improved Current Capability for HV Start-up Circuit. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4